

MOSFET - Power, Single N-Channel, SUPERFET[®], FAST, TO220FP

600 V, 100 mΩ, 27 A

NTPF100N60S5H

Description

The SUPERFET V MOSFET FAST series helps maximize system efficiency by the extremely low switching losses in hard switching application.

Features

- 650 V @ $T_J = 150^\circ\text{C}$ / Typ. $R_{DS(on)} = 80\text{ m}\Omega$
- 100% Avalanche Tested
- Pb-Free, Halogen Free / BFR Free and are RoHS Compliant

Applications

- Telecom / Server Power Supplies
- EV Charger / UPS / Solar / Industrial Power Supplies

ABSOLUTE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$, Unless otherwise noted)

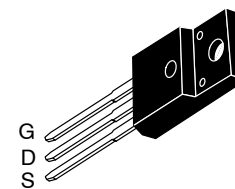
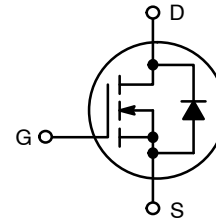
Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	600	V
Gate-to-Source Voltage	DC	V_{GS}	± 30
		AC ($f > 1\text{ Hz}$)	± 30
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	27
		$T_C = 100^\circ\text{C}$	17
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	179
Pulsed Drain Current (Note 1)	$T_C = 25^\circ\text{C}$	I_{DM}	95
		I_{SM}	95
Pulsed Source Current (Body Diode) (Note 1)			
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Source Current (Body Diode)	I_S	27	A
Single Pulse Avalanche Energy	$I_L = 5.1\text{ A}$ $R_G = 25\ \Omega$	E_{AS}	230
Avalanche Current	I_{AS}	5.1	A
Repetitive Avalanche Energy (Note 1)	E_{AR}	1.79	mJ
MOSFET dv/dt	dv/dt	120	V/ns
Peak Diode Recovery dv/dt (Note 2)		20	
Lead Temperature for Soldering Purposes (1/8" from case for 10 seconds)	T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $I_{SD} \leq 13.5\text{ A}$, $di/dt \leq 200\text{ A/s}$, $V_{DD} \leq 400\text{ V}$, starting $T_J = 25^\circ\text{C}$.

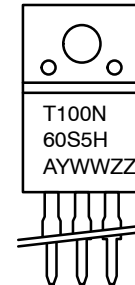
$V_{(BR)DSS}$	$R_{DS(ON)}\text{ MAX}$	$I_D\text{ MAX}$
600 V	100 mΩ @ 10 V	27 A

N-CHANNEL MOSFET



TO-220 FULLPAK
CASE 221D

MARKING DIAGRAM



T100N60S5H = Specific Device Code
 A = Assembly Location
 Y = Year
 WW = Work Week
 ZZ = Lot Code

ORDERING INFORMATION

Device	Package	Shipping
NTPF100N60S5H	TO220 FULLPACK	50 Units / Tube

NTPF100N60S5H

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.26	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}, T_J = 25^\circ\text{C}$	600	-	-	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = 10\text{ mA}$, Referenced to 25°C	-	630	-	mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}, T_J = 25^\circ\text{C}$	-	-	1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$	-	-	±100	nA

ON CHARACTERISTICS

Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 13.5\text{ A}, T_J = 25^\circ\text{C}$	-	80	100	mΩ
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 2.7\text{ mA}, T_J = 25^\circ\text{C}$	2.7	-	4.3	V
Forward Trans-conductance	g_{FS}	$V_{DS} = 20\text{ V}, I_D = 13.5\text{ A}$	-	27.1	-	S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C_{ISS}	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, f = 250\text{ kHz}$	-	2618	-	pF
Output Capacitance	C_{OSS}		-	38	-	
Time Related Output Capacitance	$C_{OSS(tr)}$	$I_D = \text{Constant}, V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$	-	608	-	
Energy Related Output Capacitance	$C_{OSS(er)}$		$V_{DS} = 0\text{ V to } 400\text{ V}, V_{GS} = 0\text{ V}$	-	64.4	
Total Gate Charge	$Q_{G(tot)}$	$V_{DD} = 400\text{ V}, I_D = 13.5\text{ A}, V_{GS} = 10\text{ V}$	-	46	-	nC
Gate-to-Source Charge	Q_{GS}		-	12.7	-	
Gate-to-Drain Charge	Q_{GD}		-	11.5	-	
Gate Resistance	R_G		$f = 1\text{ MHz}$	-	1.16	

SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 0/10\text{ V}, V_{DD} = 400\text{ V}, I_D = 13.5\text{ A}, R_G = 4.7\text{ }\Omega$	-	21.5	-	ns
Rise Time	t_r		-	5.81	-	
Turn-Off Delay Time	$t_{d(off)}$		-	61	-	
Fall Time	t_f		-	2.57	-	

SOURCE-TO-DRAIN DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_{SD} = 13.5\text{ A}, T_J = 25^\circ\text{C}$	-	-	1.2	V
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, I_{SD} = 13.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_{DD} = 400\text{ V}$	-	362	-	ns
Reverse Recovery Charge	Q_{RR}		-	5359	-	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS

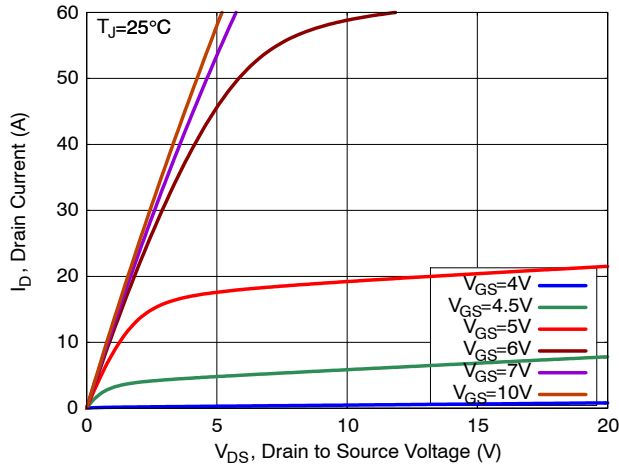


Figure 1. On-Region Characteristics

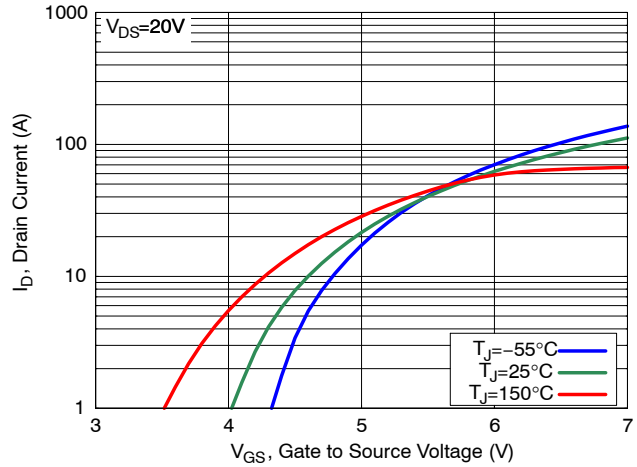


Figure 2. Transfer Characteristics

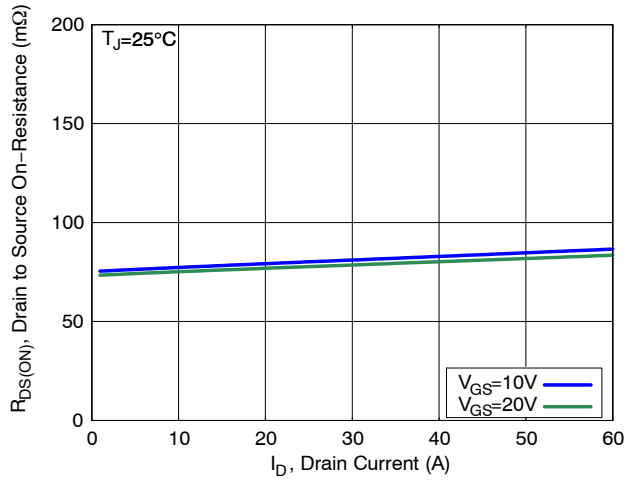


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

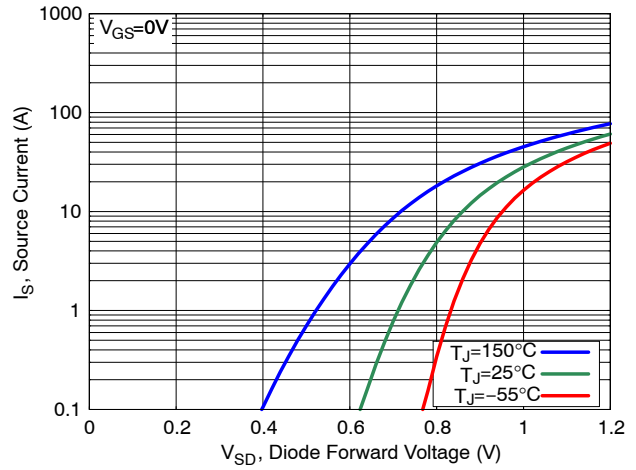


Figure 4. Diode Forward Voltage vs. Source Current

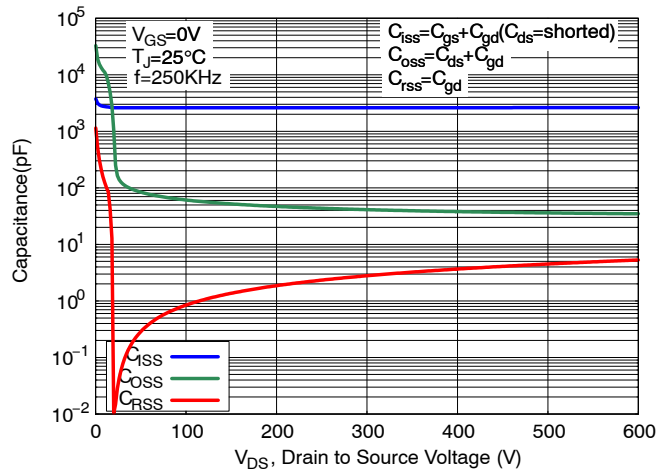


Figure 5. Capacitance Characteristics

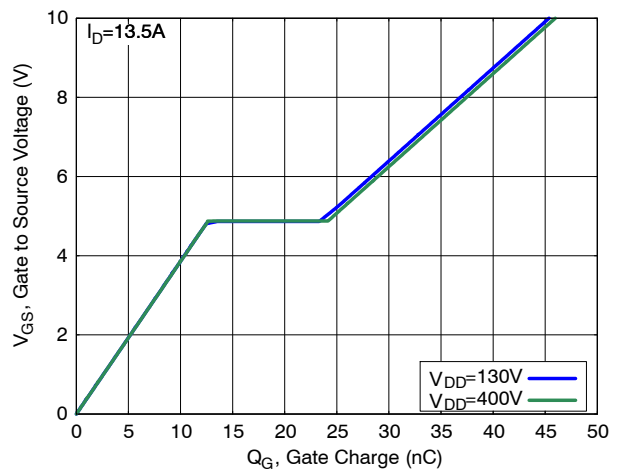


Figure 6. Gate Charge Characteristics

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TYPICAL CHARACTERISTICS

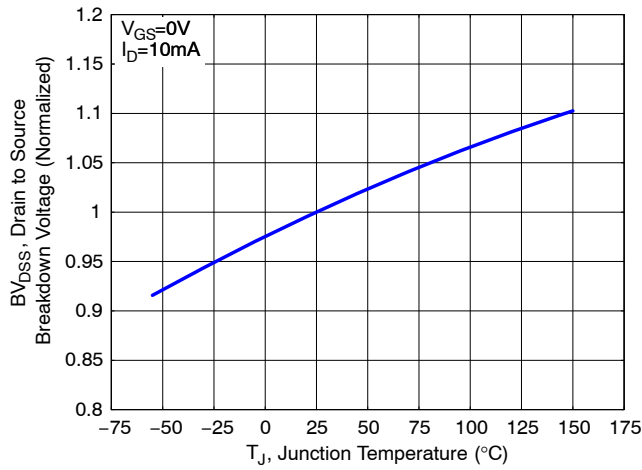


Figure 7. Breakdown Voltage Variation vs. Temperature

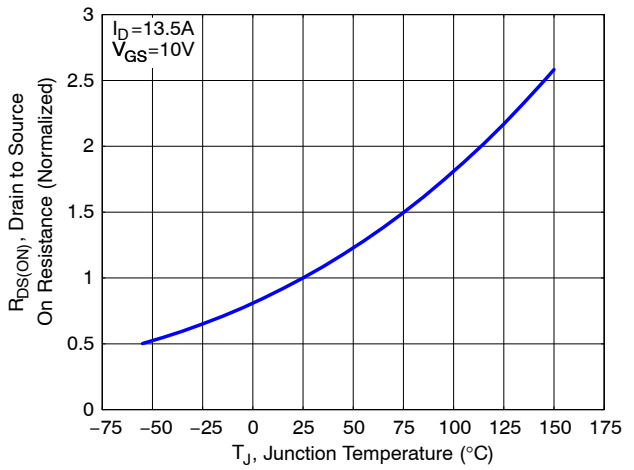


Figure 8. On-Resistance Variation vs. Temperature

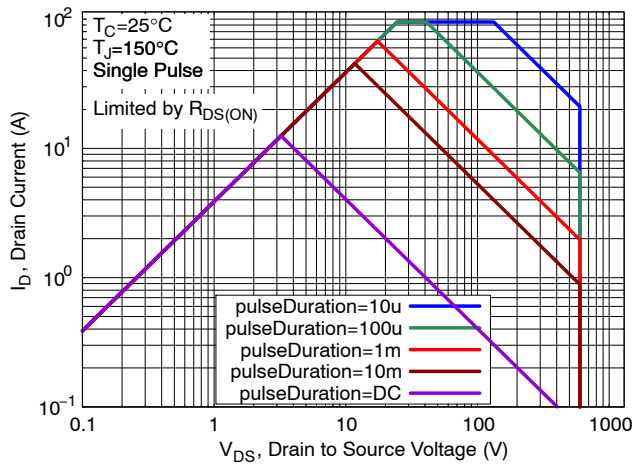


Figure 9. Maximum Safe Operating Area

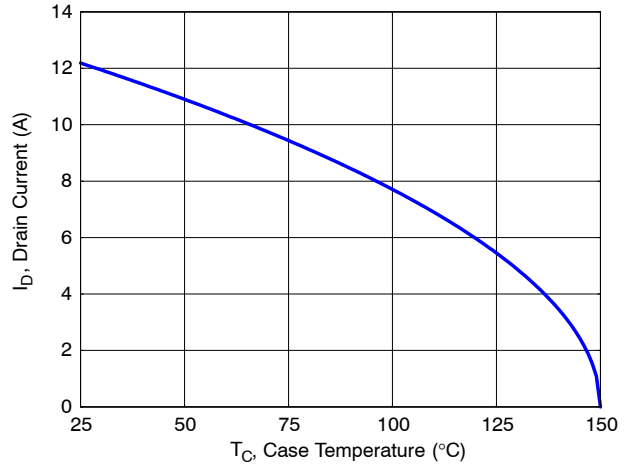


Figure 10. Maximum Drain Current vs. Case Temperature

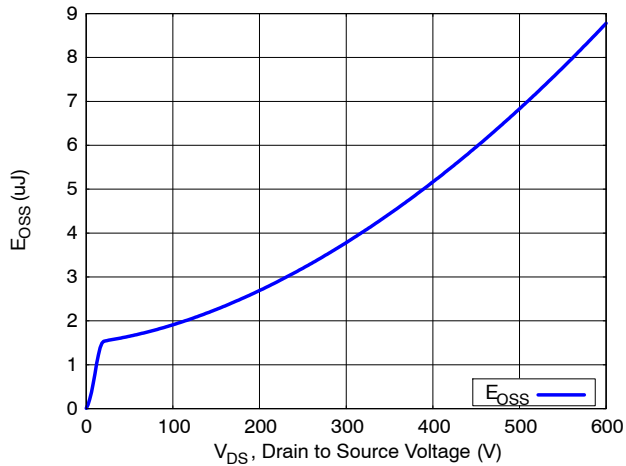


Figure 11. Eoss vs. Drain-to-Source Voltage

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TYPICAL CHARACTERISTICS

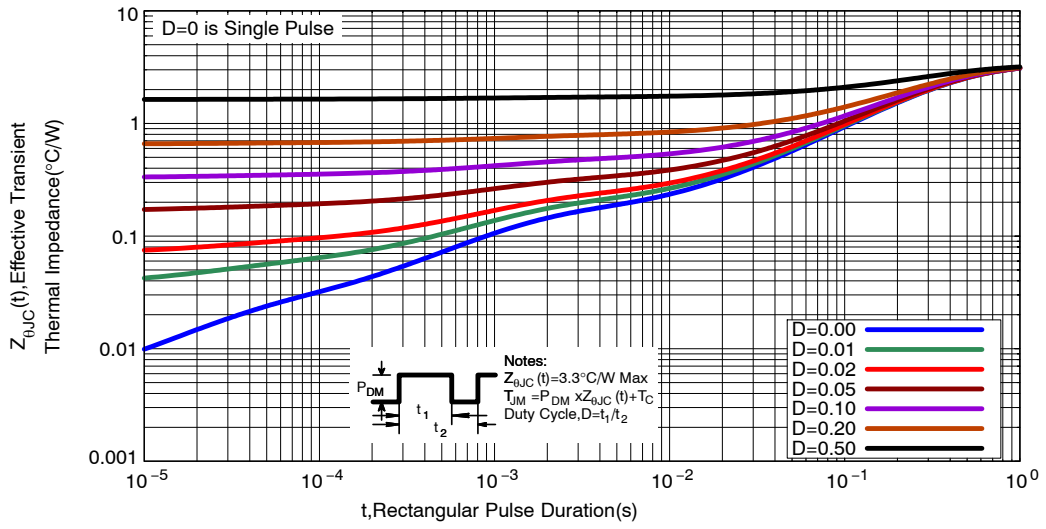
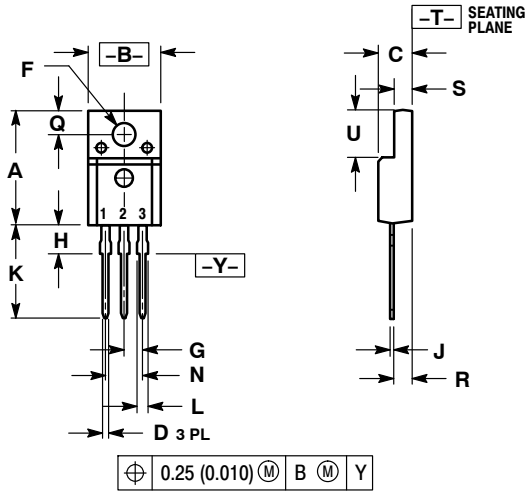


Figure 12. Transient Thermal Impedance

NTPF100N60S5H

PACKAGE DIMENSIONS

TO-220 FULLPAK CASE 221D-03 ISSUE K



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH
3. 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.617	0.635	15.67	16.12
B	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
H	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

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